## BSS63LT1G

# **High Voltage Transistor**

### **PNP Silicon**

#### **Features**

 These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V <sub>CEO</sub>	-100	Vdc
Collector – Emitter Voltage $R_{BE}$ = 10 k $\Omega$	V <sub>CER</sub>	-110	Vdc
Collector Current - Continuous	Ic	-100	mAdc

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,	P <sub>D</sub>	005	mW
(Note 1) T <sub>A</sub> = 25°C Derate above 25°C		225 1.8	mW/°C
Thermal Resistance Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2)	P <sub>D</sub>		mW
T <sub>A</sub> = 25°C		300	mW/°C
Derate above 25°C		2.4	
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	–55 to +150	°C

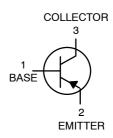
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- 1.  $FR-5 = 1.0 \times 0.75 \times 0.062$  in.
- 2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.



### ON Semiconductor®

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SOT-23 CASE 318 STYLE 6

#### **MARKING DIAGRAM**



BM = Device Code

M = Date Code\*

Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
BSS63LT1G	SOT-23 (Pb-free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

### BSS63LT1G

# **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

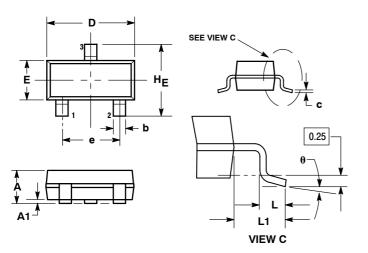
Characteristic	Symbo	ol Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage ( $I_C = -100  \mu Adc$ )	V <sub>(BR)</sub> CE	-100	_	_	Vdc
Collector – Emitter Breakdown Voltage ( $I_C$ = -10 $\mu$ Adc, $I_E$ = 0, $R_{BE}$ = 10 $k\Omega$ )	V <sub>(BR)CE</sub>	ER -110	-	-	Vdc
Collector – Base Breakdown Voltage ( $I_E = -10 \mu Adc$ , $I_E = 0$ )	V <sub>(BR)CE</sub>	-110	-	-	Vdc
Emitter – Base Breakdown Voltage (I <sub>E</sub> = –10 µAdc)	V <sub>(BR)EE</sub>	-6.0	-	-	Vdc
Collector Cutoff Current (V <sub>CB</sub> = -90 Vdc, I <sub>E</sub> = 0)	I <sub>CBO</sub>	-	-	-100	nAdc
Collector Cutoff Current ( $V_{CE} = -110 \text{ Vdc}$ , $R_{BE} = 10 \text{ k}\Omega$ )	I <sub>CER</sub>	-	-	-10	μAdc
Emitter Cutoff Current $(V_{EB} = -6.0 \text{ Vdc}, I_C = 0)$	I <sub>EBO</sub>	-	-	-200	nAdc
ON CHARACTERISTICS	•	•		•	
DC Current Gain ( $I_C$ = -10 mAdc, $V_{CE}$ = -1.0 Vdc) ( $I_C$ = -25 mAdc, $V_{CE}$ = -1.0 Vdc)	h <sub>FE</sub>	30 30	- -	- -	-
Collector – Emitter Saturation Voltage (I <sub>C</sub> = -25 mAdc, I <sub>B</sub> = -2.5 mAdc)	V <sub>CE(sa</sub>	t) _	-	-250	mVdc
Base – Emitter Saturation Voltage ( $I_C = -25$ mAdc, $I_B = -2.5$ mAdc)	V <sub>BE(sa</sub>	t) _	-	-900	mVdc
SMALL-SIGNAL CHARACTERISTICS	·		•		
Current – Gain – Bandwidth Product ( $I_C$ = –25 mAdc, $V_{CE}$ = –5.0 Vdc, f = 20 MHz)	f <sub>T</sub>	50	95	_	MHz
Case Capacitance ( $I_E = I_C = 0$ , $V_{CB} = -10$ Vdc, $f = 1.0$ MHz)	C <sub>C</sub>	-	-	20	pF

<sup>1.</sup> FR-5 =  $1.0 \times 0.75 \times 0.062$  in. 2. Alumina =  $0.4 \times 0.3 \times 0.024$  in. 99.5% alumina.

#### BSS63LT1G

#### PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 **ISSUE AN** 



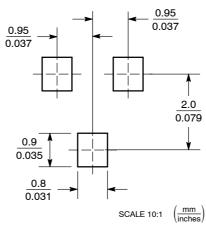
- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
  MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF
- BASE MATERIAL. 318-01 THRU -07 AND -09 OBSOLETE, NEW STANDARD 318-08.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	MOM	MAX
Α	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
С	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104

STYLE 6: PIN 1.

- BASE
- 2. **EMITTER**
- COLLECTOR

#### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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